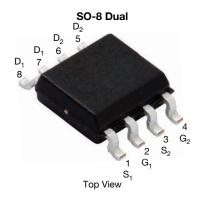
SQ4949EY

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Vishay Siliconix

Automotive Dual P-Channel 30 V (D-S) 175 °C MOSFET

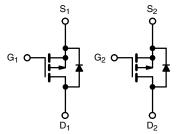


| PRODUCT SUMMARY | | | | |
|--------------------------------------------|-------|--|--|--|
| V _{DS} (V) | -30 | | | |
| $R_{DS(on)}(\Omega)$ at V_{GS} = - 10 V | 0.035 | | | |
| $R_{DS(on)}(\Omega)$ at V_{GS} = - 4.5 V | 0.065 | | | |
| I _D (A) per leg | -7.5 | | | |
| Configuration | Dual | | | |

FEATURES

- TrenchFET[®] Power MOSFET
- 100 % R_q and UIS tested
- AEC-Q101 qualified ^c
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





P-Channel MOSFET P-Channel MOSFET

| ORDERING INFORMATION | | | | |
|---------------------------------|-----------------------------------------------------------------------------|--|--|--|
| Package | SO-8 | | | |
| Lead (Pb)-free and halogen-free | SQ4949EY (for detailed order number please see www.vishay.com/doc?79771) | | | |

| PARAMETER | | SYMBOL | LIMIT | UNIT |
|----------------------------------------------|-------------------------|-----------------------------------|-------------|------|
| Drain-source voltage | | V _{DS} | -30 | V |
| Gate-source voltage | | V _{GS} | ± 20 | V |
| Continuous drain current | T _C = 25 °C | 1 | -7.5 | |
| | T _C = 125 °C | I _D | -4.3 | |
| Continuous source current (diode conduction) | | I _S | -3 | A |
| Pulsed drain current ^a | | I _{DM} | -30 | |
| Single pulse avalanche current | L = 0.1 mH | I _{AS} | -17 | |
| Single pulse avalanche energy | | E _{AS} | 14 | mJ |
| Maximum power dissipation ^a | T _C = 25 °C | D | 3.3 | W |
| | T _C = 125 °C | P _D | 1.1 | vv |
| Operating junction and storage temperature | e range | T _J , T _{stg} | -55 to +175 | °C |

| THERMAL RESISTANCE RATINGS | | | | | |
|----------------------------|------------------------|-------------------|-------|------|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Junction-to-ambient | PCB mount ^b | R _{thJA} | 110 | °C/W | |
| Junction-to-foot (drain) | | R _{thJF} | 45 | 0/10 | |

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. When mounted on 1" square PCB (FR-4 material)

c. Parametric verification ongoing

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SQ4949EY

| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
|-----------------------------------------------|--------------------------|---------------------------------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------|------|-------|-------|------|
| Static | | | | | • | | |
| Drain-source breakdown voltage | V _{DS} | $V_{GS} = 0 V, I_D = -250 \mu A$ | | -30 | - | - | v |
| Gate-source threshold voltage | V _{GS(th)} | V _{DS} = | $V_{DS} = V_{GS}, I_D = -250 \ \mu A$ | | -2.0 | -2.5 | |
| Gate-source leakage | I _{GSS} | $V_{DS} = 0 V, V_{GS} = \pm 20 V$ | | - | - | ± 100 | nA |
| | | $V_{GS} = 0 V$ | V _{DS} = -30 V | - | - | -1.0 | |
| Zero gate voltage drain current | I _{DSS} | $V_{GS} = 0 V$ | $V_{DS} = -30 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$ | - | - | -50 | μA |
| | | $V_{GS} = 0 V$ | $V_{DS} = -30 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$ | - | - | -150 | 1 |
| On-state drain current ^a | I _{D(on)} | V _{GS} = -10 V | $V_{DS} \le -5 V$ | -20 | - | - | Α |
| | | V _{GS} = -10 V | I _D = -5.9 A | - | 0.028 | 0.035 | |
| Durin country on state unitations of | | V _{GS} = -10 V | I _D = -5.9 A, T _J = 125 °C | - | - | 0.051 | Ω |
| Drain-source on-state resistance ^a | R _{DS(on)} | $V_{GS} = -10 V$ | I _D = -5.9 A, T _J = 175 °C | - | - | 0.059 | |
| | | V _{GS} = -4.5 V | I _D = -4 A | - | 0.051 | 0.065 | |
| Forward transconductance b | g _{fs} | V _{DS} = | -15 V, I _D = -5.9 A | - | 12 | - | S |
| Dynamic ^b | | | | | • | | |
| Input capacitance | C _{iss} | | V _{DS} = -25 V, f = 1 MHz | - | 816 | 1020 | pF |
| Output capacitance | C _{oss} | $V_{GS} = 0 V$ | | - | 168 | 210 | |
| Reverse transfer capacitance | C _{rss} | | | - | 116 | 145 | |
| Total gate charge ^c | Qg | | | - | 19.5 | 30 | |
| Gate-source charge ^c | Q _{gs} | V _{GS} = -10 V | $V_{DS} = -15 \text{ V}, \text{ I}_{D} = -4.9 \text{ A}$ | - | 3.1 | - | nC |
| Gate-drain charge ^c | Q _{gd} | | | - | 4.7 | - | |
| Gate resistance | Rg | f = 1 MHz | | 4 | - | 12 | Ω |
| Turn-on delay time ^c | t _{d(on)} | | | - | 7 | 11 | |
| Rise time ^c | tr | V_{DD} = - 15 V, R _L = 15 Ω I _D \cong -1 A, V _{GEN} = -10 V, R _g = 1 Ω | | - | 9 | 14 | 1 |
| Turn-off delay time ^c | t _{d(off)} | | | - | 28 | 42 | - ns |
| Fall time ^c | t _f | | | - | 8 | 12 | |
| Source-Drain Diode Ratings and Char | acteristics ^b | | | | • | | |
| Pulsed current ^a | I _{SM} | | | - | - | -30 | Α |
| Forward voltage | V _{SD} | I _F = -5 A, V _{GS} = 0 V | | _ | -0.85 | -1.2 | V |

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

b. Guaranteed by design, not subject to production testing

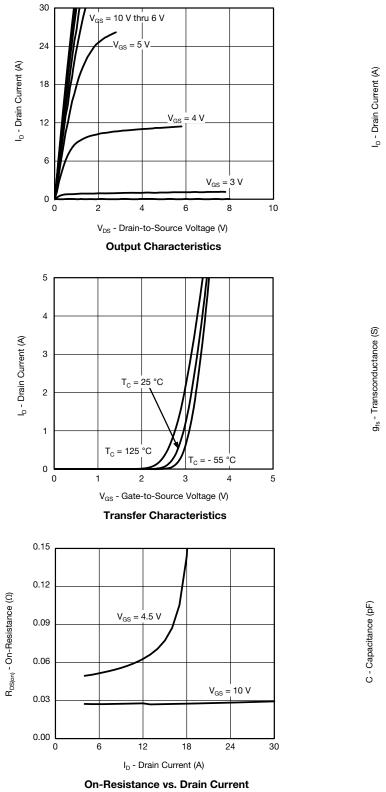
c. Independent of operating temperature

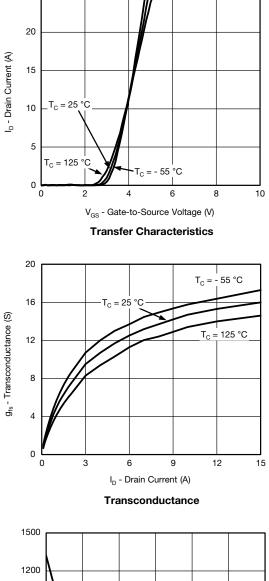
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)





25

1200 900 G_{iss} C_{iss} C_{rss} C_{rss} C

Capacitance

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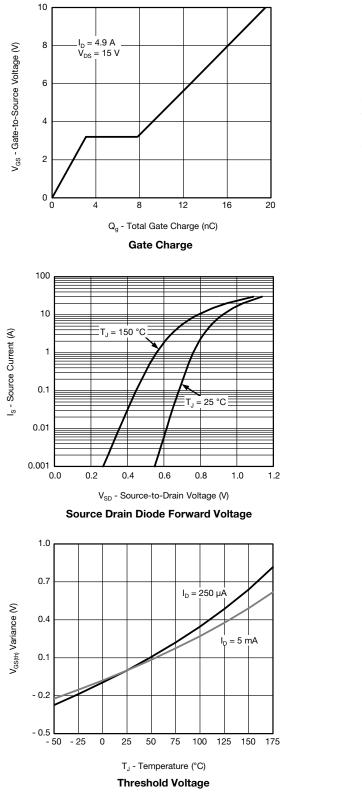
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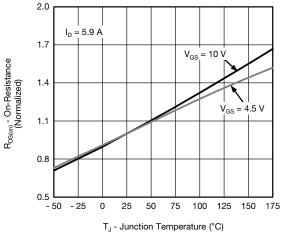
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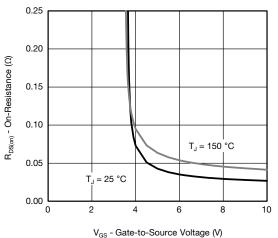


TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

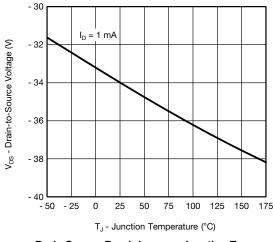




On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

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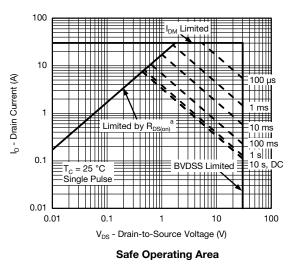
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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

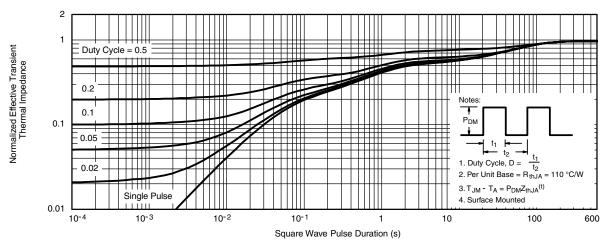


Note

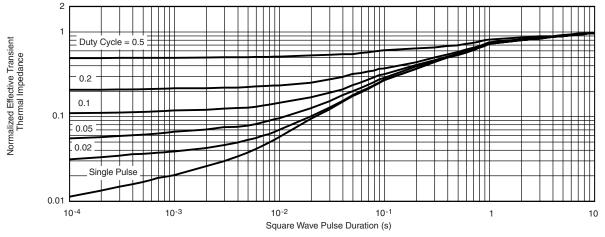
a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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Package Information

Vishay Siliconix

SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





| | MILLIMETERS | | INC | IES | |
|---------------------------------------------|-------------|------|-----------|-------|--|
| DIM | Min | Мах | Min | Max | |
| A | 1.35 | 1.75 | 0.053 | 0.069 | |
| A ₁ | 0.10 | 0.20 | 0.004 | 0.008 | |
| В | 0.35 | 0.51 | 0.014 | 0.020 | |
| С | 0.19 | 0.25 | 0.0075 | 0.010 | |
| D | 4.80 | 5.00 | 0.189 | 0.196 | |
| E | 3.80 | 4.00 | 0.150 | 0.157 | |
| е | 1.27 | BSC | 0.050 BSC | | |
| н | 5.80 | 6.20 | 0.228 | 0.244 | |
| h | 0.25 | 0.50 | 0.010 | 0.020 | |
| L | 0.50 | 0.93 | 0.020 | 0.037 | |
| q | 0° | 8° | 0° | 8° | |
| S | 0.44 | 0.64 | 0.018 | 0.026 | |
| ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498 | | | | | |

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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